

Three-electron bunches in occupation of a 5-site Coulomb cluster

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Attraction of like charges in a localized system implies that, upon increasing the Fermi energy, the occupation of the system changes as $n \rightarrow (n+2)$, while the occupation, $(n+1)$, is skipped. In this way, the attraction translates into the bunching of electrons. For a localized system of $N = 4$ sites, attraction of electrons manifests itself in skipping of $n = 2$ occupation. The origin of the attraction is rearrangement of the occupations of the surrounding sites which plays the role of a polaronic effect. We consider an $N = 5$ -site cluster and demonstrate that, with screened Coulomb repulsion, *three-electron* bunching becomes possible, i.e. the change of occupation $n = 1 \rightarrow n = 4$ with $n = 2$ and $n = 3$ occupations skipped.

PACS numbers:

I. INTRODUCTION

A question whether two electrons can attract each other without lattice dynamics involved was previously posed in many papers. Another formulation of this question is whether the formation of negative- U centers,¹ which are believed to be due to phonons, is possible as a result of electron-electron repulsion. An appeal of having purely electronic negative- U centers is that such centers can be viewed as precursors of purely electronic superconducting state.

On the theory side, electron attraction in the repulsive systems was invoked to (i) explain the valence-skipping phenomenon, see e.g. Refs. 2–6, when the valence of certain elements does not occur in the compounds which they form; (ii) derive pairing within certain limits of the Hubbard model,⁷ which, essentially, amounts to replacing phonons by magnons.⁸ Also, as demonstrated in Ref. 9, formation of charge-2e excitations, “trimers”, is favored in doped transition-metal dichalcogenide bilayers near the half-filling. The origin of pairing in Ref. 9 with two type of sites having different energy is reduction of

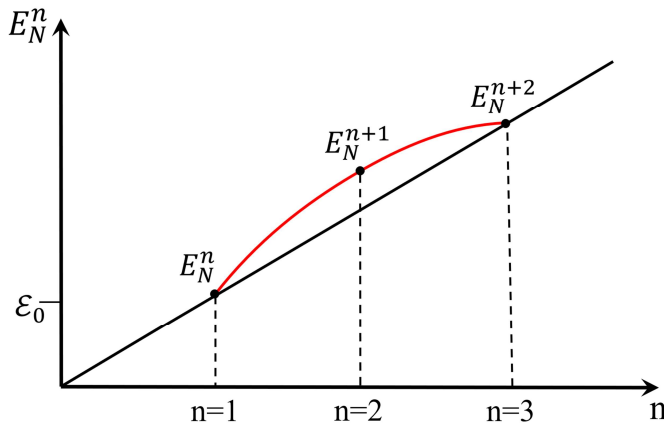


FIG. 1: A criterion, $E_N^n + E_N^{n+2} < 2E_N^{n+1}$, of the attraction of two electrons implies a concavity of the curve E_N^n . As a result, the population evolves as $n \rightarrow (n+2)$.

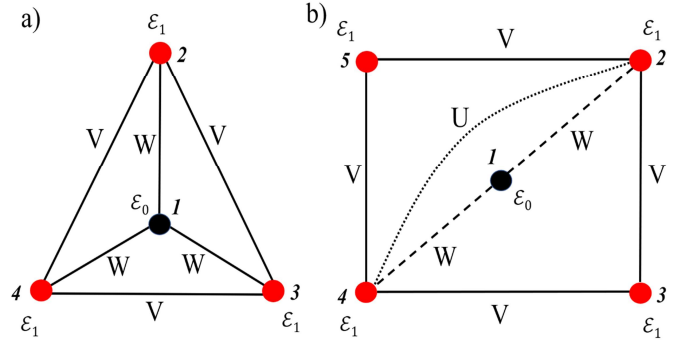


FIG. 2: a) Illustration of the 4-site model. The energy of the central site, ϵ_0 , is smaller than the energies of the corner sites, ϵ_1 . For a purely Coulomb system, the repulsions, W and V , are related as $3^{1/2}$. For a gate-screened interaction they are related as $3^{3/2}$; b) Illustration of the 5-site model. The repulsions W , U , and V are related as $2 : 2^{1/2} : 1$ for a purely Coulomb interaction and as $2^3 : 2^{3/2} : 1$ for the gate-screened interaction.

electrostatic energy which dominates over the kinetic energy. Minimal model of a trimer requires four sites. Note that such a 4-site model of pairing was previously studied in Ref. 10 in different relation.

On the experimental side, attention to the issue of possible attraction of localized electrons was drawn by the early experiments.^{11–13} In these experiments, one-by-one magneto-tunneling events of electrons from an electrode into a big semiconductor island. Certain portion of events revealed bunching of electrons into pairs. Accounting this bunching by attraction of electrons within a 4-site model encounters a problem that incoherent tunneling of two electrons takes too much time. Later experiments^{14,15} suggested that two-electron events take place at the edge and are related to the formation of the edge states in magnetic field.

Demonstration of pairing due to repulsion on a truly microscopic level was reported in Ref. 16. Experimental

setup in Ref. 16 was very similar to the 4-site cluster (2-site polarizer and double-well quantum dot). In a certain domain of gate voltages, one dot of a double-well system was either empty or accommodated a pair of electrons as a result of reoccupation of the dots constituting the polarizer.

Due to flexibility of their nanotube-based technique, the authors of Ref. 16 suggested several variants for scaling-up their setup. In particular, their approach can tackle the question whether more complex many-particle processes can be realized experimentally. In this paper we demonstrate that, adding one extra site to the 4-site model, opens a possibility of *three-electron* bunches. To establish a criterion for such three-electron bunches, we introduce E_N^n , which is a minimal energy of n electrons in a cluster of N sites. Next electron enters the cluster when the Fermi level position in surrounding system is equal to

$$\mu_1 = E_N^{n+1} - E_N^n. \quad (1)$$

Two electrons enter the cluster at

$$\mu_2 = \frac{E_N^{n+2} - E_N^n}{2}. \quad (2)$$

Formation of a $2e$ pair takes place when $\mu_2 < \mu_1$, i.e. when the usual condition $(E_N^{n+2} + E_N^n) < 2E_N^{n+1}$, illustrated in Fig. I, is met. Continuing the reasoning, three electrons enter the cluster at

$$\mu_3 = \frac{E_N^{n+3} - E_N^n}{3}. \quad (3)$$

Then a $3e$ -bunch is favored over single-electron and $2e$ -bunch under the conditions $\mu_3 < \mu_1$ and $\mu_3 < \mu_2$.

II. TWO-ELECTRON BUNCHING IN A 4-SITE CLUSTER

For didactic reasons, in this section we review the steps unveiling the two-electron bunching in the 4-site model. Extension to the 5-site model involves all the similar steps. On the other hand, the flow of logics offers an insight about possible extensions.

Step I. A 4-site cluster is illustrated in Fig. 2a. We examine the evolution of the minimal energy of configurations with varying n . The 4-site cluster is completely filled when $n=4$, i.e. only one configuration is possible. It is also obvious that, for $n = 1$, the minimal energy corresponds to filling the central site with energy $\varepsilon_0 < \varepsilon_1$. Thus $E_4^1 = \varepsilon_0$. When $n = 2$, the electron in the center can either stay there or move to the vertex in order to reduce the potential energy. Thus, the candidates for E_4^2 are

$$\tilde{E}_4^2 = \varepsilon_0 + \varepsilon_1 + W \text{ or } \tilde{E}_4^2 = 2\varepsilon_1 + V. \quad (4)$$

Equally, there are two candidates to minimize the energy when the population of the cluster is $n = 3$, namely

$$\tilde{E}_4^3 = \varepsilon_0 + 2\varepsilon_1 + 2W + V \text{ or } \tilde{E}_4^3 = 3\varepsilon_1 + 3V. \quad (5)$$

Step II. At this step, we make two crucial assumptions: $\tilde{E}_4^2 < \tilde{E}_4^3$ and $\tilde{E}_4^3 > \tilde{E}_4^2$, which translate into the following inequalities

$$\begin{aligned} 2\varepsilon_1 + V &> \varepsilon_0 + \varepsilon_1 + W, \\ 3\varepsilon_1 + 3V &< \varepsilon_0 + 2\varepsilon_1 + V + 2W. \end{aligned} \quad (6)$$

These inequalities imply that it is energetically unfavorable for two electrons to vacate the center, but it is favorable for three electrons to vacate the center. Note that Eq. (6) can be presented in a concise form

$$1 - \frac{V}{W} < \frac{\varepsilon_1 - \varepsilon_0}{W} < 2 \left(1 - \frac{V}{W} \right). \quad (7)$$

When the conditions Eq. (6) are met, we have

$$E_4^2 = \tilde{E}_4^2, \quad E_4^3 = \tilde{E}_4^3. \quad (8)$$

Step III. At this step we require that the dependence E_4^n is “concave”, as illustrated in Fig. I. Using Eq. (8), the pairing condition $E_4^1 + E_4^3 < 2E_4^2$ takes the form

$$\varepsilon_0 + 3(\varepsilon_1 + V) < 2(\varepsilon_0 + \varepsilon_1 + W). \quad (9)$$

Note that the above condition restricts the energy difference between the center and the vertex sites: $\frac{\varepsilon_1 - \varepsilon_0}{W} < 2 - \frac{3V}{W}$.

Step IV. We now go back to the assumptions made above, Eq. (7), and test whether they are consistent with concavity. This test is illustrated in Fig. 4. We see that the second inequality is satisfied automatically. To satisfy the first inequality, one needs $V < \frac{W}{2}$. As seen from Fig. 2a, for purely Coulomb interaction, the relation between V and W is $V = \frac{W}{3^{1/2}}$. Thus, the first condition is not satisfied. It can be, however, satisfied if the gate is present at a distance, d , above the plane of the cluster. Then the Coulomb interaction, $V(\rho) = \frac{e^2}{\rho}$, gets modified to $V(\rho) = e^2 \left[\frac{1}{\rho} - \frac{1}{(\rho^2 + 4d^2)^{1/2}} \right]$. Then, for $\rho \gg d$, we have $V = \frac{W}{3^{3/2}} < \frac{W}{2}$, so that in the domain

$$W - V < \varepsilon_1 - \varepsilon_0 < 2W - 3V, \quad (10)$$

shown in Fig. 4a with red, $2e$ -pairing is possible.

III. THREE-ELECTRON BUNCHING IN A 5-SITE CLUSTER

We now generalize the reasoning from the previous section to the 5-site model illustrated in Fig. 2b. The central site is surrounded by four vertexes. Three repulsion energies, shown in the figure, are related as $U < V < W$ in accordance with distances between the corresponding sites. Similarly to the 4-site model, we assume that the energy, ε_0 , of the central site is lower than ε_1 -the energy of the vertex sites. Obviously, $E_5^1 = \varepsilon_0$. Our strategy

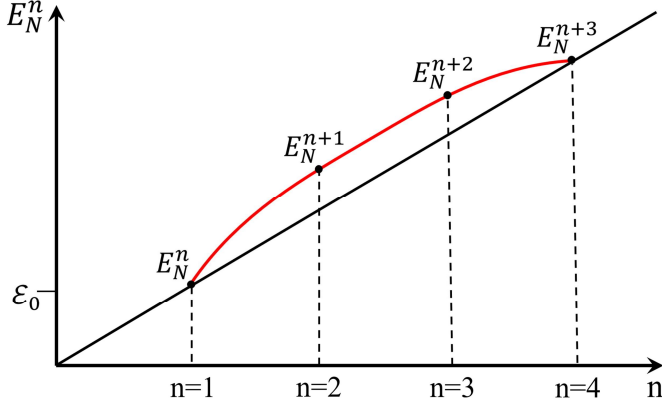


FIG. 3: Illustration of three-electron bunching in the cluster of N sites. The bunch is possible under the conditions $\frac{1}{3}(E_N^{n+3} - E_N^n) < \frac{1}{2}(E_N^{n+2} - E_N^n) < E_N^{n+1} - E_N^n$.

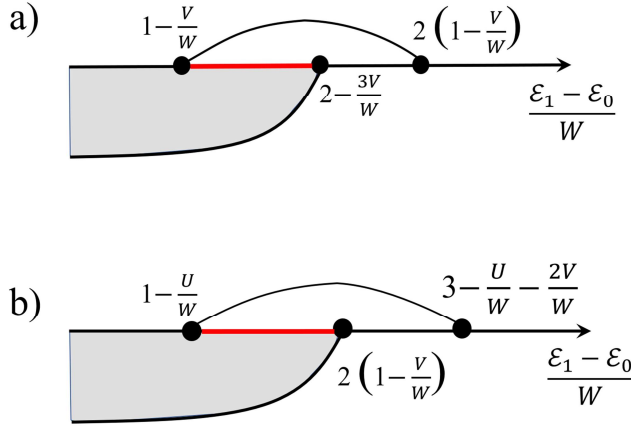


FIG. 4: Different domains of the dimensionless imbalance, $\frac{\epsilon_1 - \epsilon_0}{W}$, of the site energies: a) 4-site model. In the domain of imbalances, $\left\{1 - \frac{V}{W}, 2\left(1 - \frac{V}{W}\right)\right\}$ the energy of two-electron configuration is minimal when one electron occupies the central site, while for three-electron configuration the energy is minimal when all three electrons reside in the vertices. In the grey region the condition of concavity, illustrated in Fig. 1, is satisfied, so that 2e-pairing occurs in the domain marked with red. b) 5-site model. In the red domain the occupation of the cluster with chemical potential evolves as $n = 1 \rightarrow n = 4$.

in a search for three-electron bunching is based on the argument that, by placing electrons in the vertexes, the configuration loses in its on-site energy, but gains due to the reduction in potential energy.

Step I. There are three candidates for the double occupation of the cluster. They are

$$\tilde{E}_5^2 = \epsilon_0 + \epsilon_1 + W \text{ or } \tilde{E}_5^2 = 2\epsilon_1 + V \text{ or } \left(\tilde{\tilde{E}}\right)_5^2 = 2\epsilon_1 + U. \quad (11)$$

Since $V > U$, the energy \tilde{E}_5^2 is smaller than $\tilde{\tilde{E}}_5^2$ leaving us with only two candidates. One can also see that there

are three candidates for the triple occupation, namely

$$\tilde{E}_5^3 = 3\epsilon_1 + 2V + U \text{ or } \tilde{\tilde{E}}_5^3 = 2\epsilon_1 + \epsilon_0 + 2W + U, \text{ or } \left(\tilde{\tilde{E}}\right)_5^3 = 2\epsilon_1 + \epsilon_0 + 2W + V. \quad (12)$$

We can now compare \tilde{E}_5^3 to $\left(\tilde{\tilde{E}}\right)_5^3$ and realize that the latter has higher energy since $V > U$. This, again, leaves us with two candidates for $\tilde{\tilde{E}}_5^3$.

Finally, the occupation of the cluster with four electrons is possible in two configurations having different energies. These energies are

$$\tilde{E}_5^4 = \epsilon_0 + 3\epsilon_1 + 3W + 2V + U, \text{ or } \tilde{\tilde{E}}_5^4 = 4\epsilon_1 + 4V + 2U. \quad (13)$$

Obviously, the state with energy, $\tilde{\tilde{E}}_5^4$ is four-fold degenerate depending on which vertex is empty.

Step II. At this point, we make three crucial assumptions:

1. $\tilde{\tilde{E}}_5^2 > \tilde{E}_5^2$,
2. $\tilde{\tilde{E}}_5^3 > \tilde{E}_5^3$,
3. $\tilde{\tilde{E}}_5^4 < \tilde{E}_5^4$.

The assumptions are made in order to ensure that the ground states with $n = 2$ and $n = 3$ include the center site, while the ground state with $n = 4$ includes the sites in the vertexes. Using Eqs. (11), (12), (13), the above assumptions can be rewritten as

$$\epsilon_0 + \epsilon_1 + W < 2\epsilon_1 + U \Rightarrow 1 - \frac{U}{W} < \frac{\epsilon_1 - \epsilon_0}{W}, \quad (14)$$

$$\begin{aligned} \epsilon_0 + 2\epsilon_1 + 2W + U &> 3\epsilon_1 + 2V + U \\ \Rightarrow 2\left(1 - \frac{V}{W}\right) &> \frac{\epsilon_1 - \epsilon_0}{W}, \end{aligned} \quad (15)$$

$$\begin{aligned} \epsilon_0 + 3\epsilon_1 + 3W + 2V + U &> 4\epsilon_1 + 4V + 2U \\ \Rightarrow 3 - \frac{2V}{W} - \frac{U}{W} &> \frac{\epsilon_1 - \epsilon_0}{W}. \end{aligned} \quad (16)$$

Now it is convenient to restructure the above inequalities into two separate ranges as

$$\begin{aligned} 1 - \frac{U}{W} &< \frac{\epsilon_1 - \epsilon_0}{W} < 2\left(1 - \frac{V}{W}\right), \\ 1 - \frac{U}{W} &< \frac{\epsilon_1 - \epsilon_0}{W} < 3 - 2\frac{V}{W} - \frac{U}{W}. \end{aligned} \quad (17)$$

Whether the three-electron bunches are allowed or not depends on whether or not the domains Eq. (17) overlap, as illustrated in Fig. 4b. After making the above

assumptions we can specify the ground-state configuration for each n , namely

$$E_5^2 = \tilde{E}_5^2, E_5^3 = \tilde{E}_5^3, E_5^4 = \tilde{E}_5^4 \quad (18)$$

Step III. We now require that the ground-state energies E_5^n are arranged as shown in Fig. 3, or, in other words, we require that these energies satisfy the conditions

$$\frac{1}{3} (E_5^4 - E_5^1) < \frac{1}{2} (E_5^3 - E_5^1) < E_5^2 - E_5^1. \quad (19)$$

The first and the second conditions can be cast into a traditional form

$$\begin{aligned} \frac{\varepsilon_1 - \varepsilon_0}{W} &> 2\frac{V}{W} + \frac{U}{W}, \\ \frac{\varepsilon_1 - \varepsilon_0}{W} &< 3 - 4\frac{V}{W} - 2\frac{U}{W}. \end{aligned} \quad (20)$$

We see that, in the same way as Eq. (17), the necessary requirements for 3-e bunches restrict the asymmetry in single-electron energies both from below and from the above.

IV. Now a nontrivial question arises: is there a domain in which the conditions Eq. (17) and Eq. (20) are consistent with each other? It is apparent that for purely

Coulomb repulsion the requirements Eq. (20) cannot be met. Indeed, with purely Coulomb interaction, one has $\frac{U}{W} = \frac{1}{2}$, while $\frac{V}{W} = \frac{1}{2^{1/2}}$. Then the right-hand side in the second inequality Eq. (20) is *negative*. Turning to screened Coulomb repulsion, we have $\frac{U}{W} = \frac{1}{8}$, while $\frac{V}{W} = \frac{1}{2^{3/2}}$. Then Eq. (17) places the asymmetry, $\frac{\varepsilon_1 - \varepsilon_0}{W}$, into the interval (0.875, 1.29). At the same time, Eq. (20) restricts the asymmetry to the interval (0.83, 0.95). We see that two restricting intervals overlap proving that 3e-bunches are allowed.

IV. CONCLUSION

Certainly the conditions for the formation of 3e-bound state in the repulsive system are more restrictive than the conditions for the formation of the 2e-bound state. We do not know whether the bunches containing more than three electrons are possible, but our finding motivates to search for them.

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